DUSEU

Configurable Multifunction Gate NLV7SZ57

The NLV7SZ57 is an advanced high-speed CMOS multifunction gate. The device allows the user to choose logic functions AND, OR, NAND, NOR, XNOR, INVERT and BUFFER. The device has Schmitt-trigger inputs, thereby enhancing noise immunity.

Features

- Designed for 1.65 V to 5.5 V V_{CC} Operation
- 3.3 ns t_{PD} at $V_{CC} = 5 V (Typ)$
- Inputs/Outputs Overvoltage Tolerant up to 5.5 V
- IOFF Supports Partial Power Down Protection
- Sink 24 mA at 3.0 V
- Chip Complexity < 100 FETs
- endorse of the second of the s • NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant



DIAGRAMS 6 XXXM=

o

MARKING



= Pb-Free Package

SC-88/SC70-6/

SOT-363

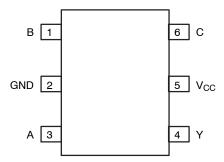
CASE 419B-02

(Note: Microdot may be in either location or may not be present)

*Date Code orientation and/or position may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 8 of this data sheet.





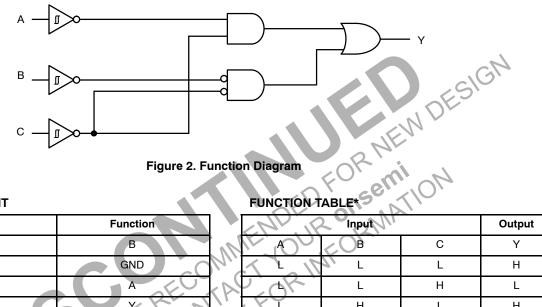


Figure 2. Function Diagram

PIN	ASSIGNMENT
	ACCIMINENT

Pin	Function
1	В
2	GND
3	A
4	Y K
5	Vec
6	S'SF,TA
THISDEVIC	REPRESENT

CNU	Input		Output
	COB	С	Y
		L	Н
	L	Н	L
ΥĽ	Н	L	Н
L	Н	Н	Н
Н	L	L	L
Н	L	Н	L
Н	Н	L	L
Н	Н	Н	Н

*To select a logic function, please refer to "Logic Configurations section".

LOGIC CONFIGURATIONS

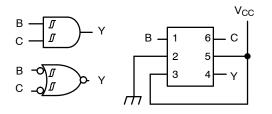


Figure 3. 2-Input AND (When A = "H")

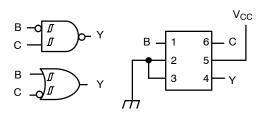


Figure 4. 2–Input NAND with input B inverted (When A = "L")

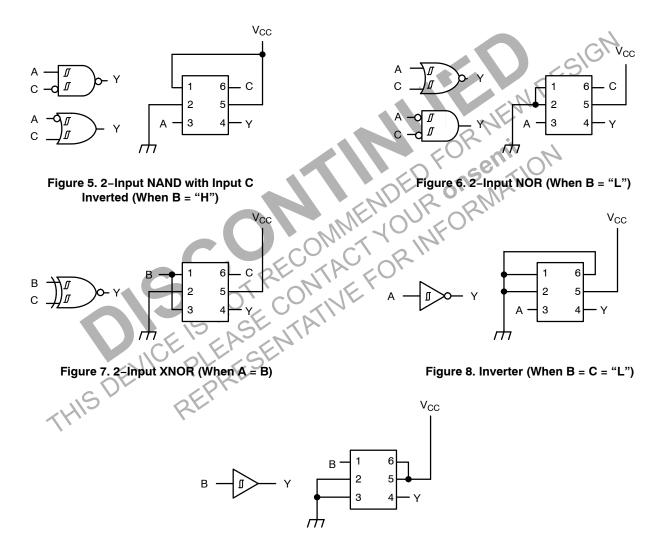


Figure 9. Buffer (When A = "L" and C = "H")

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage	-0.5 to +7.0	V
V _{IN}	DC Input Voltage	-0.5 to +7.0	V
V _{OUT}	DC Output Voltage Active–Mode (High or Low State) Tri–State Mode (Note 1) Power–Down Mode (V _{CC} = 0 V)	$\begin{array}{c} -0.5 \text{ to } V_{CC} + 0.5 \\ -0.5 \text{ to } +7.0 \\ -0.5 \text{ to } +7.0 \end{array}$	V
I _{IK}	DC Input Diode Current V _{IN} < GND	-50	mA
I _{OK}	DC Output Diode Current V _{OUT} < GND	-50	mA
I _{OUT}	DC Output Source/Sink Current	±50	mA
I_{CC} or I_{GND}	DC Supply Current per Supply Pin or Ground Pin	±100	mA
T _{STG}	Storage Temperature Range	-65 to +150	°C
ΤL	Lead Temperature, 1 mm from Case for 10 Secs	260	°C
Т _Ј	Junction Temperature Under Bias	+150	°C
θ_{JA}	Thermal Resistance (Note 2) SC-88	377	°C/W
PD	Power Dissipation in Still Air SC-88	-332	mW
MSL	Moisture Sensitivity	Level 1	
F _R	Flammability Rating Oxygen Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	
V _{ESD}	ESD Withstand Voltage (Note 3) Human Body Mode Charged Device Model Charged Device Model	>2000 >200 N/A	V
ILATCHUP	Latchup Performance (Note 4)	±500	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. Applicable to devices with outputs that may be tri-stated.
- Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2 ounce copper trace no air flow per JESD51-7.
 CDM tested to EIA/JESD22-C101-F. JEDEC recommends that ESD qualification to EIA/JESD22-A115-A (Machine Model) be discontinued and USD204 an per JEDEC/JEP172A. 4. Tested to EIA/JESD78 Class II. TACE

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Мах	Unit
V _{CC}	Positive DC Supply Voltage	1.65	5.5	V
V _{IN}	DC Input Voltage	0	5.5	V
V _{OUT}	DC Output Voltage Active-Mode (High or Low State) Tri-State Mode (Note 1) Power-Down Mode (V _{CC} = 0 V)	0	V _{CC} 5.5 5.5	V
T _A	Operating Free-Air Temperature	-55	+125	°C
t _r , t _f	Input Rise or Fall Rate $V_{CC} = 1.65 \text{ V to } 1.95 \text{ V} \\ V_{CC} = 2.3 \text{ V to } 2.7 \text{ V} \\ V_{CC} = 3.0 \text{ V to } 3.6 \text{ V} \\ V_{CC} = 4.5 \text{ V to } 5.5 \text{ V} \\ \end{array}$	0 0	No Limit No Limit No Limit No Limit	nS/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

			V _{cc}	1	Γ _A = 25°(c	–40°C 85	≤ T _A ≤ °C		≤ T _A ≤ 5°C	
Symbol Parameter	Parameter	Condition	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V_{T+}	Positive Input		1.65	0.79	-	1.16	-	1.16	-	1.16	V
	Threshold Voltage		2.3	1.11	-	1.56	-	1.56	-	1.56	
			3.0	1.5	-	1.87	-	1.87	_	1.87	
			4.5	2.16	-	2.74	-	2.74	-	2.74	
			5.5	2.61	-	3.33	-	3.33	-	3.33	
V_{T-}	Negative Input		1.65	0.35	-	0.62	0.35	-	0.35	-	V
	Threshold Voltage		2.3	0.58	-	0.87	0.58	-	0.58	-	
			3.0	0.84	-	1.19	0.84	-	0.84	-	
			4.5	1.41	-	1.9	1.41	1	1.41	-	
			5.5	1.78	-	2.2	1.78	-	1.78	(G)	•
V _H	Negative Input		1.65	0.3	-	0.62	0.3	0.62	0.3	0.62	V
	Threshold Voltage		2.3	0.4	-	0.8	0.4	0.8	0.4	0.8	
			3.0	0.53	-	0.87	0.53	0.87	0.53	0.87	
			4.5	0.71	1	1.04	0.71	1.04	0.71	1.04	
		5.5	0.8	ł	1.2	0.8	1.2	0.8	1.2		
V _{OH}	High-Level Output Voltage	I _{OH} = -50 μA	1.65 to 5.5	V _{CC} - 0.1	Vcc	ED	V _{CC} - 0.1		V _{CC} - 0.1	-	V
	$V_{IN} = V_{IH}$ or V_{IL}	I _{OH} = -4 mA	1.65	1.20	1.52	.12	1.20	<u>77</u>	1.20	_	
		I _{OH} = -8 mA	2.3	1.9	2.1	$) - \langle \langle$	1.9	-	1.9	-	
		I _{OH} = -16 mA	3	2.4	2.7	H2	2.4	-	2.4	-	
		I _{OH} = -24 mA	3	2.3	2.5	-	2.3	-	2.3	-	-
		I _{OH} = -32 mA	4.5	3.8	4	-	3.8	-	3.8	-	
V _{OL}	Low–Level Output Voltage	1 _{OL} = 100 µA	1.65 to 5.5	(P_{1})	-	0.1	-	0.1	-	0.1	V
	$V_{IN} = V_{IH}$ or V_{IL}	l _{OL} = 4 mA	1.65	_	0.08	0.45	-	0.45	-	0.45	
	V _{IN} = V _{IH} or V _{IL}	I _{OL} =8mA	2.3	_	0.2	0.3	-	0.3	-	0.4	
	DE	l _{OL} = 16 mA	3	-	0.28	0.4	-	0.4	-	0.5	
4	JIS Y	I _{OL} = 24 mA	3	_	0.38	0.55	-	0.55	_	0.55	
		I _{OL} = 32 mA	4.5	_	0.42	0.55	-	0.55	_	0.65	
I _{IN}	Input Leakage Current	V _{IN} = 5.5 V or GND	1.65 to 5.5	-	-	+0.1	-	+1.0	-	+1.0	μA
I _{OFF}	Power Off Leakage Current	V_{IN} = 5.5 V or V _{OUT} = 5.5 V	0	-	-	1.0	-	10	-	10	μA
I _{CC}	Quiescent Supply Current	V _{IN} = 5.5 V or GND	5.5	-	-	1.0	-	10	_	10	μA

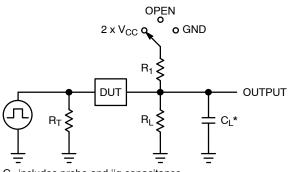
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AC ELECTRICAL CHARACTERISTICS

				1	Γ _A = 25°0	;		≤ T _A 5°C		≤ T _A 25°C	
Symbol	Parameter	Condition	V _{CC} (V)	Min	Тур	Max	Min	Max	Min	Max	Unit
t _{PLH} , t _{PHL} Propagation Delay, (A or B or C) to Y (Figures 10 and 11)	$\begin{array}{l} R_L = 1 \ k\Omega, \\ C_L = 30 \ pF \end{array}$	1.65 to 1.95	-	8.6	14.4	-	14.4	-	14.4	ns	
	$\begin{array}{l} R_{L} = 500 \; \Omega, \\ CL = 30 \; pF \end{array}$	2.3 to 2.7	-	5.1	8.3	-	8.3	-	8.3		
	$R_{L} = 500 \Omega$,	3.0 to 3.6	-	3.9	6.3	-	6.3	-	6.3		
		C _L = 50 pF	4.5 to 5.5	-	3.3	5.1	-	5.1	-	5.1	

CAPACITIVE CHARACTERISTICS

	Parameter	Condition	Typical	Unit
C _{IN}	Input Capacitance	$V_{CC} = 5.5 \text{ V}, V_{IN} = 0 \text{ V or } V_{CC}$	2.5	pF
C _{OUT}	Output Capacitance	V_{CC} = 5.5 V, V_{IN} = 0 V or V_{CC}	4.0	pF
C _{PD}	Power Dissipation Capacitance (Note 5)	10 MHz, $V_{CC} = 3.3 \text{ V}$, $V_{IN} = 0 \text{ V}$ or V_{CC} 10 MHz, $V_{CC} = 5.0 \text{ V}$, $V_{IN} = 0 \text{ V}$ or V_{CC}	16 19.5	pF
Average power co	operating ourrept can be obtained by the equation: I	ance which is calculated from the operating current co CC(OPR) = CPD • VCC • fin + ICC. CPD is used to determ	ing the ne los	ithout Ic

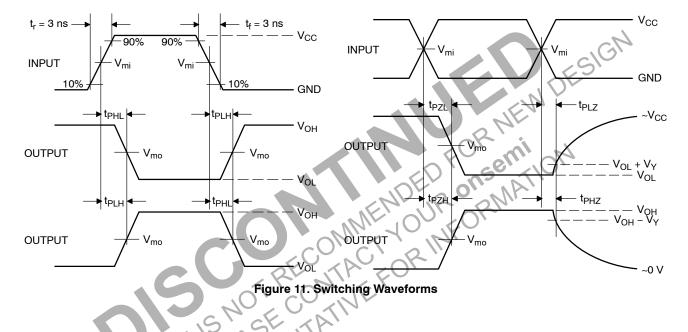


Test	Switch Position	C _L , pF	R_{L}, Ω	R ₁ , Ω		
t _{PLH} / t _{PHL}	Open	See AC Characteristics Table				
t _{PLZ} / t _{PZL}	$2 \times V_{CC}$	50	500	500		
t _{PHZ} / t _{PZH}	GND	50	500	500		

X = Don't Care

 C_L includes probe and jig capacitance R_T is Z_{OUT} of pulse generator (typically 50 $\Omega)$ f = 1 MHz

Figure 10. Test Circuit



	CEEEAS	V _m	_o , V	
V _{CC} , V	V _{mi} , v	t _{PLH} , t _{PHL}	t _{PZL} , t _{PLZ} , t _{PZH} , t _{PHZ}	V _Y , V
1.65 to 1.95	V _{CC} /2	V _{CC} / 2	V _{CC} / 2	0.15
2.3 to 2.7	V _{OC} /2	V _{CC} / 2	V _{CC} / 2	0.15
3.0 to 3.6	V _{CC} / 2	V _{CC} / 2	V _{CC} / 2	0.3
4.5 to 5.5	V _{CC} / 2	V _{CC} / 2	V _{CC} / 2	0.3

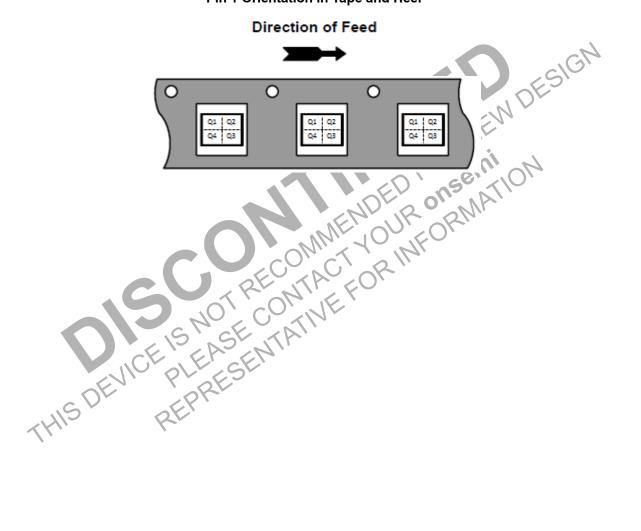
ORDERING INFORMATION

Device	Package	Specific Device Code	Pin 1 Orientation (See below)	Shipping [†]
NL7SZ57DFT2G-L22348	SC–88 (Pb–Free)	MN	Q4	3000 / Tape & Reel
NLV7SZ57DFT2G*	SC-88 (Pb-Free)	MN	Q4	3000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

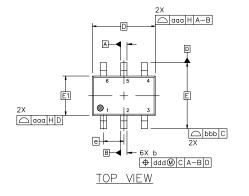
Pin 1 Orientation in Tape and Reel



SC-88 2.00x1.25x0.90, 0.65P CASE 419B-02 **ISSUE Z**

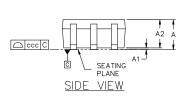
DATE 18 APR 2024

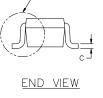
DUSEM



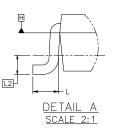
NOTES:

- DIMENSIONING AND TOLERANCING CONFORM TO ASME 1. Y14.5-2018.
- 2.
- ALL DIMENSION ARE IN MILLIMETERS. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 3. PER END.
- 4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF DATUMS A AND B ARE DETERMINED AT DATUM H.
- 5.
- DIMENSIONS & AND C APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP. DIMENSION & DOES NOT INCLUDE DAMBAR PROTRUSION. 6.
- 7 ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION & AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

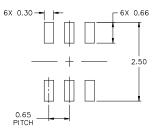




DETAIL A



	MILLIMETERS					
DIM	MIN.	NOM.	MAX.			
A			1.10			
A1	0.00		0.10			
A2	0.70	0.90	1.00			
b	0.15	0.20	0.25			
с	0.08	0.15	0.22			
D		2.00 BSC	;			
E		2.10 BSC				
E1		1.25 BSC	;			
е		0.65 BSC)			
L	0.26	0.36	0.46			
L2	0.15 BSC					
aaa	0.15					
bbb	0.30					
ccc		0.10				
ddd		0.10				



RECOMMENDED MOUNTING FOOTPRINT*

FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

XXX = Specific Device Code = Date Code* Μ

GENERIC **MARKING DIAGRAM***

XXXM-

0

6

= Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

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SC-88 2.00x1.25x0.90, 0.65P CASE 419B-02 ISSUE Z

DATE 18 APR 2024

STYLE 1: PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2	STYLE 2: CANCELLED	STYLE 3: CANCELLED	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. COLLECTOR 4. EMITTER 5. BASE 6. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	STYLE 6: PIN 1. ANODE 2 2. N/C 3. CATHODE 1 4. ANODE 1 5. N/C 6. CATHODE 2
STYLE 7: PIN 1. SOURCE 2 2. DRAIN 2 3. GATE 1 4. SOURCE 1 5. DRAIN 1 6. GATE 2	STYLE 8: CANCELLED	STYLE 9: PIN 1. EMITTER 2 2. EMITTER 1 3. COLLECTOR 1 4. BASE 1 5. BASE 2 6. COLLECTOR 2	STYLE 10: PIN 1. SOURCE 2 2. SOURCE 1 3. GATE 1 4. DRAIN 1 5. DRAIN 2 6. GATE 2	STYLE 11: PIN 1. CATHODE 2 2. CATHODE 2 3. ANODE 1 4. CATHODE 1 5. CATHODE 1 6. ANODE 2	STYLE 12: PIN 1. ANODE 2 2. ANODE 2 3. CATHODE 1 4. ANODE 1 5. ANODE 1 6. CATHODE 2
STYLE 13:	STYLE 14:	STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:
PIN 1. ANODE	PIN 1. VREF	PIN 1. ANODE 1	PIN 1. BASE 1	PIN 1. BASE 1	PIN 1. VIN1
2. N/C	2. GND	2. ANODE 2	2. EMITTER 2	2. EMITTER 1	2. VCC
3. COLLECTOR	3. GND	3. ANODE 3	3. COLLECTOR 2	3. COLLECTOR 2	3. VOUT2
4. EMITTER	4. IOUT	4. CATHODE 3	4. BASE 2	4. BASE 2	4. VIN2
5. BASE	5. VEN	5. CATHODE 2	5. EMITTER 1	5. EMITTER 2	5. GND
6. CATHODE	6. VCC	6. CATHODE 1	6. COLLECTOR 1	6. COLLECTOR 1	6. VOUT1
STYLE 19:	STYLE 20:	STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:
PIN 1. I OUT	PIN 1. COLLECTOR	PIN 1. ANODE 1	PIN 1. D1 (i)	PIN 1. Vn	PIN 1. CATHODE
2. GND	2. COLLECTOR	2. N/C	2. GND	2. CH1	2. ANODE
3. GND	3. BASE	3. ANODE 2	3. D2 (i)	3. Vp	3. CATHODE
4. V CC	4. EMITTER	4. CATHODE 2	4. D2 (c)	4. N/C	4. CATHODE
5. V EN	5. COLLECTOR	5. N/C	5. VBUS	5. CH2	5. CATHODE
6. V REF	6. COLLECTOR	6. CATHODE 1	6. D1 (c)	6. N/C	6. CATHODE
STYLE 25:	STYLE 26:	STYLE 27:	STYLE 28:	STYLE 29:	STYLE 30:
PIN 1. BASE 1	PIN 1. SOURCE 1	PIN 1. BASE 2	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. SOURCE 1
2. CATHODE	2. GATE 1	2. BASE 1	2. DRAIN	2. ANODE	2. DRAIN 2
3. COLLECTOR 2	3. DRAIN 2	3. COLLECTOR 1	3. GATE	3. COLLECTOR	3. DRAIN 2
4. BASE 2	4. SOURCE 2	4. EMITTER 1	4. SOURCE	4. EMITTER	4. SOURCE 2
5. EMITTER	5. GATE 2	5. EMITTER 2	5. DRAIN	5. BASE/ANODE	5. GATE 1
6. COLLECTOR 1	6. DRAIN 1	6. COLLECTOR 2	6. DRAIN	6. CATHODE	6. DRAIN 1

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

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